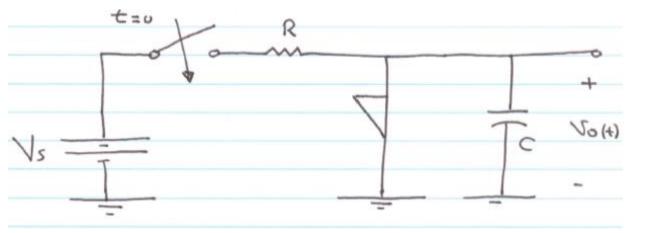
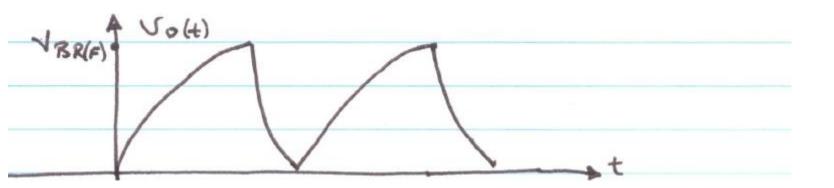


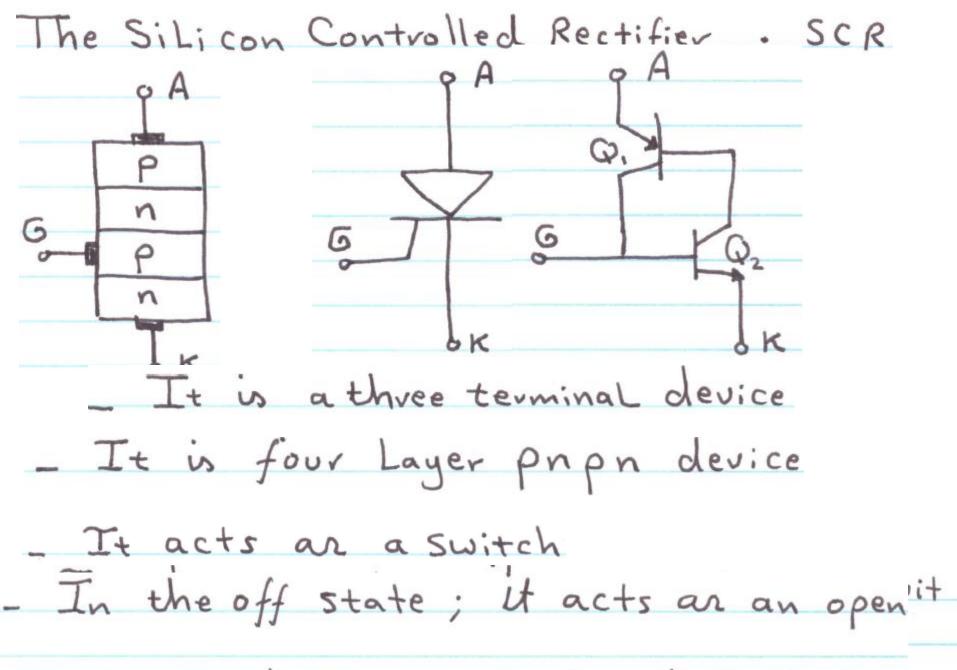
* When the anode Current IA drops back

.

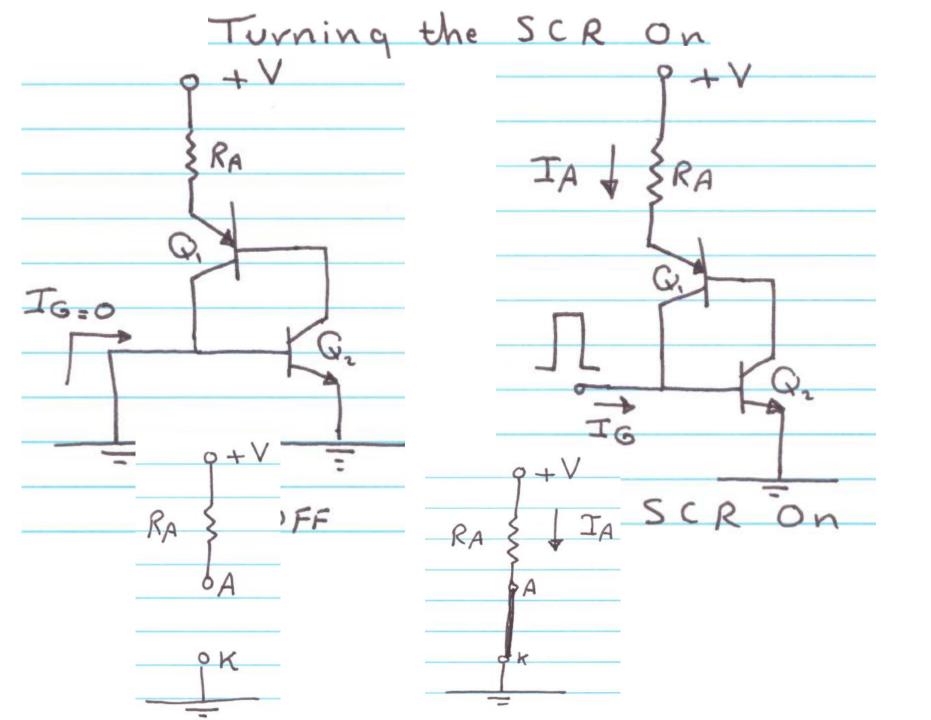


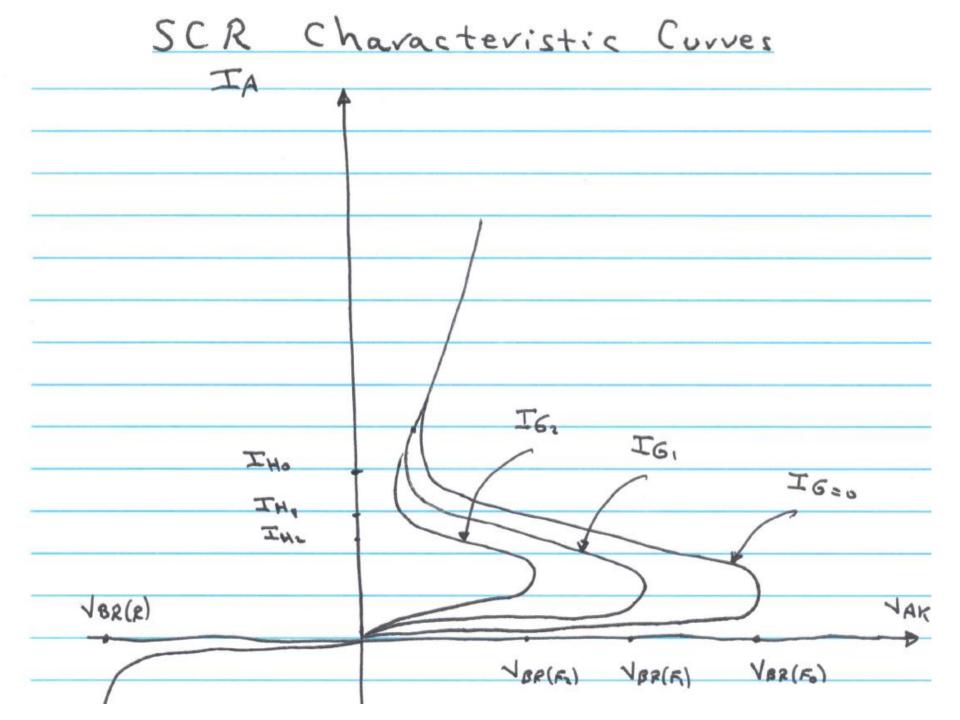
The Capacitor rapidly discharge through the device until IA < IH The device switch back to the offstate

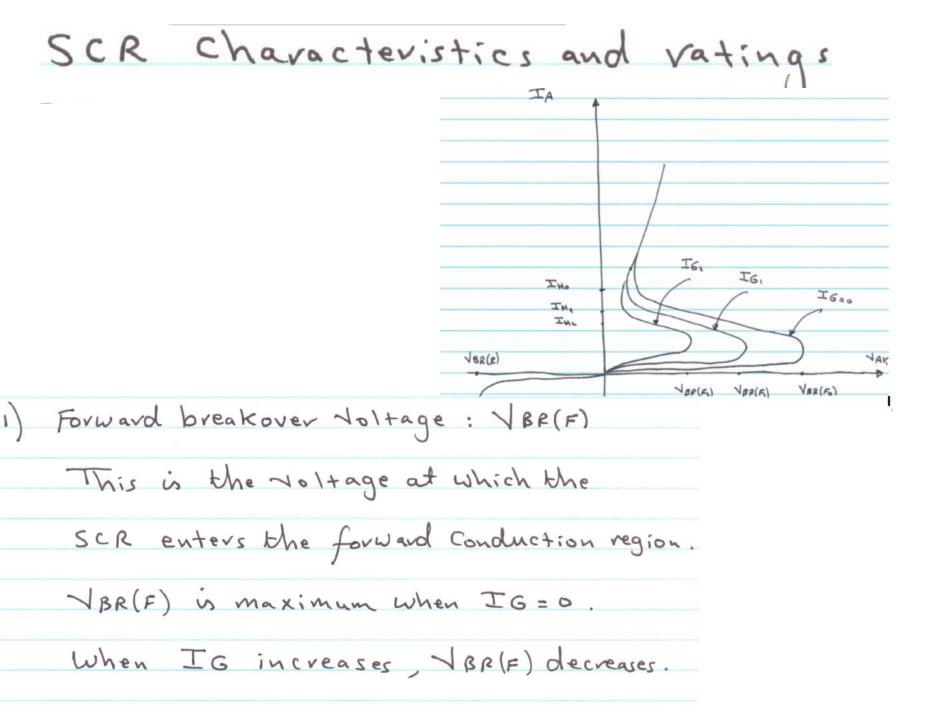


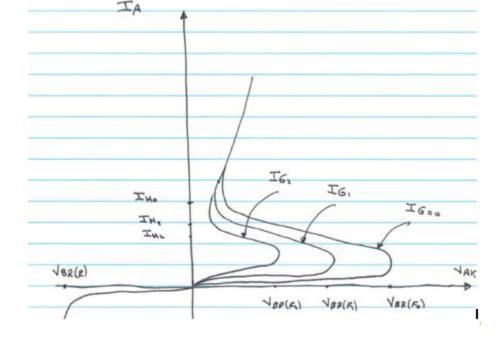


Circuit between Anode and Cathod

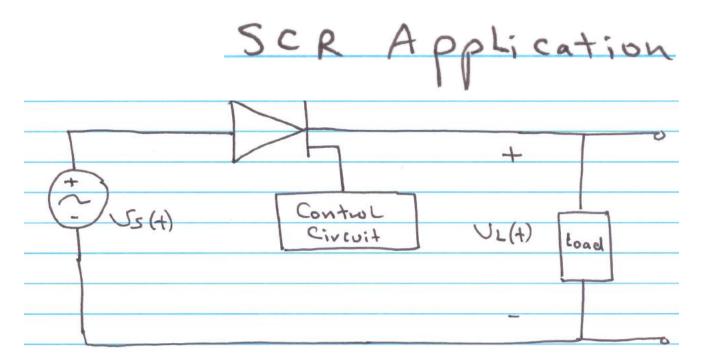


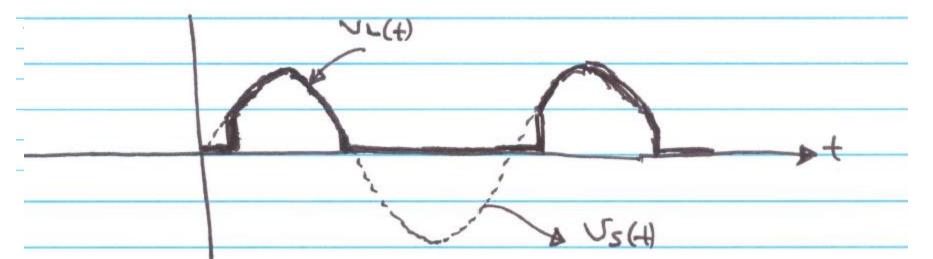


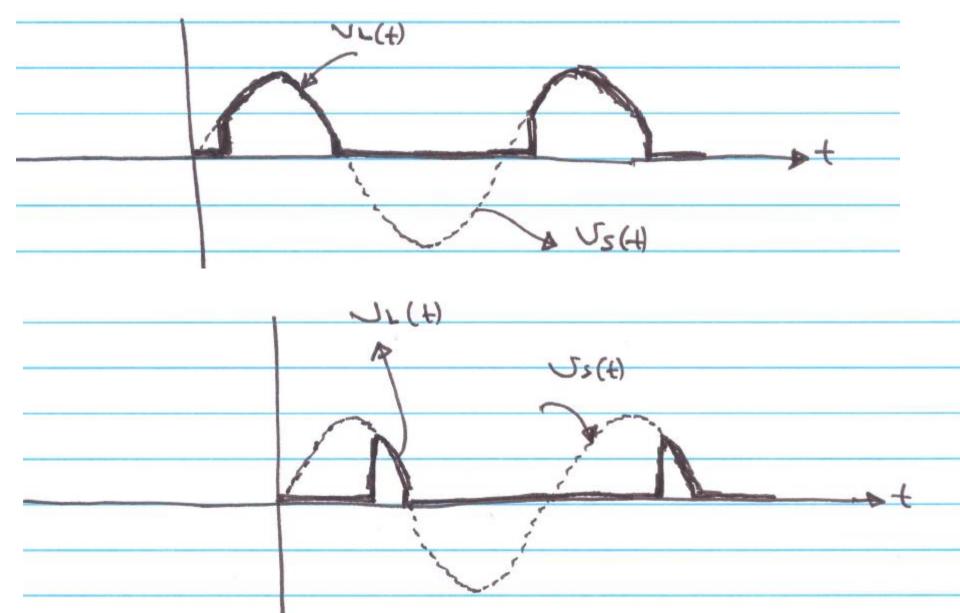


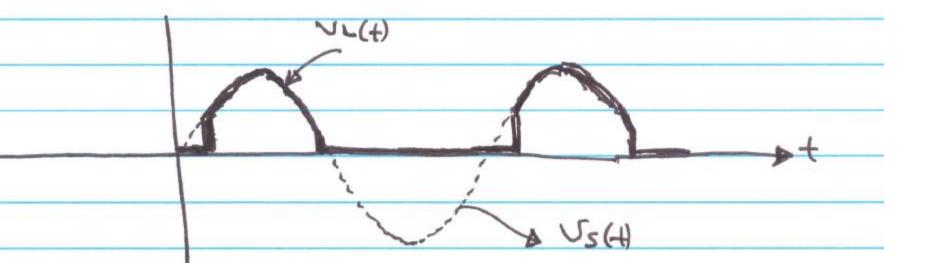


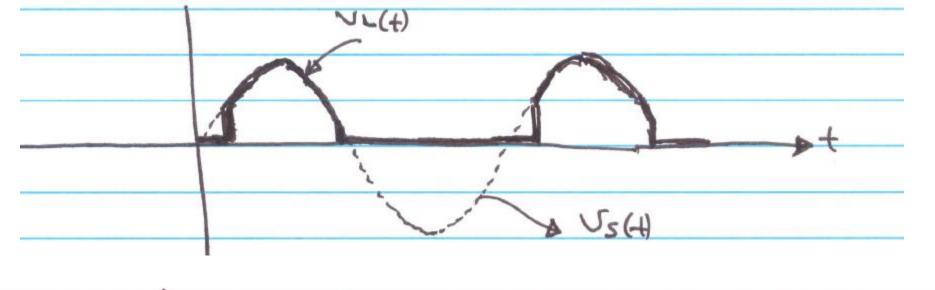
5 Forward blocking region , This region Correspond to the OFF Condition of the SCR where the forward Current from anode to Cathod is blocked by the open Civcuit of the SCR.

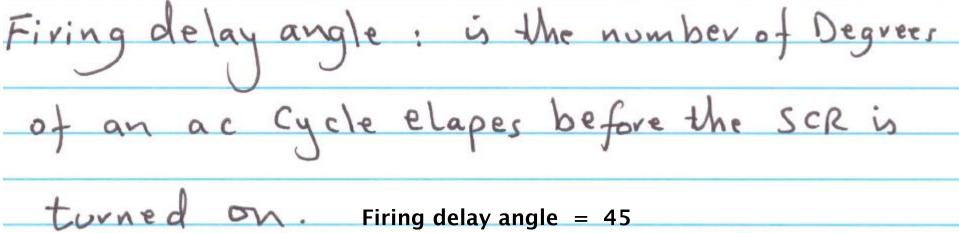




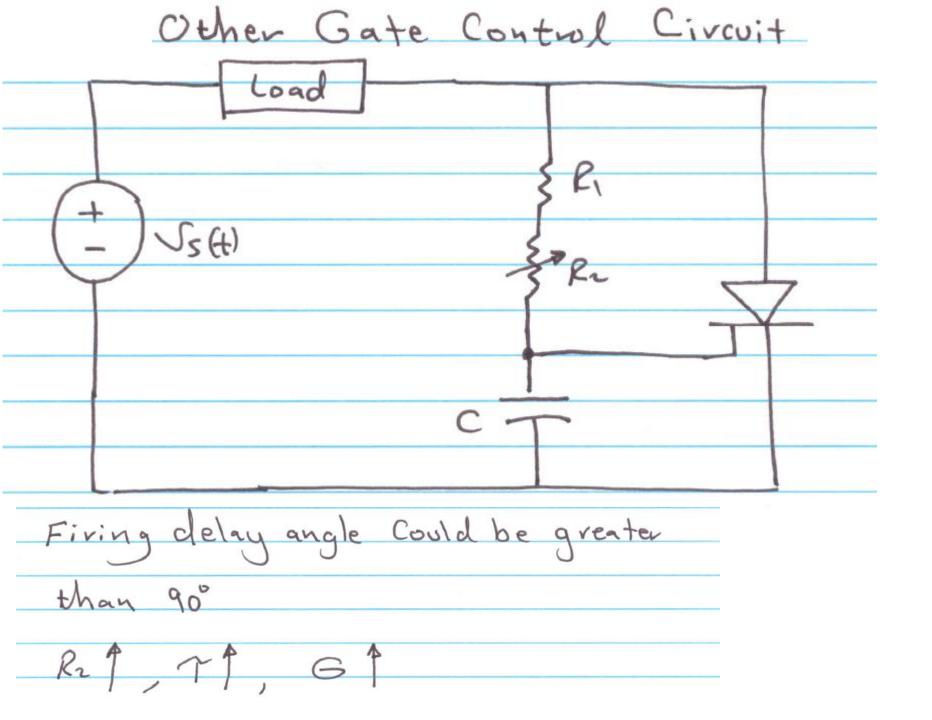






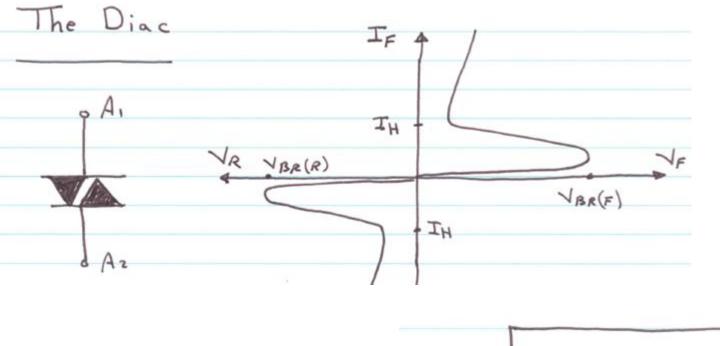


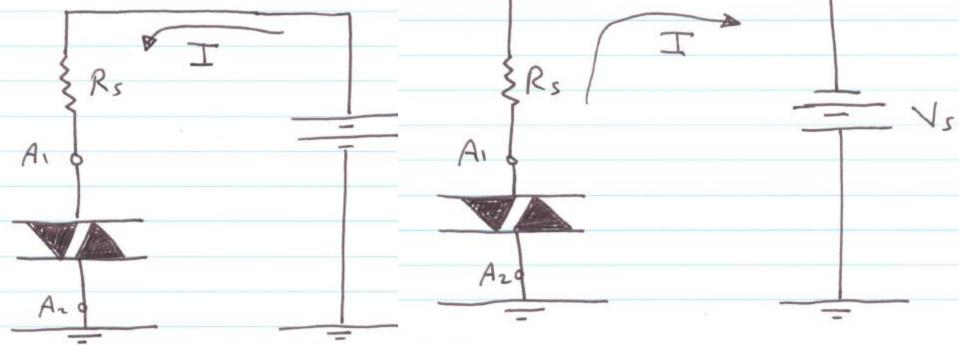
Typical Gate Control Circoits Load RI) NS (+) R

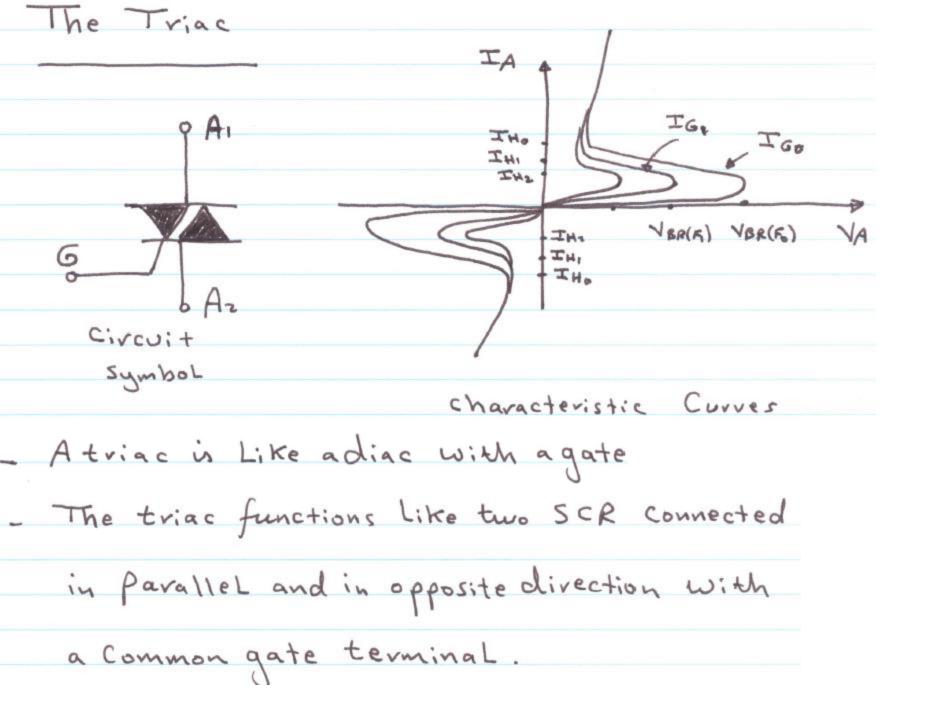


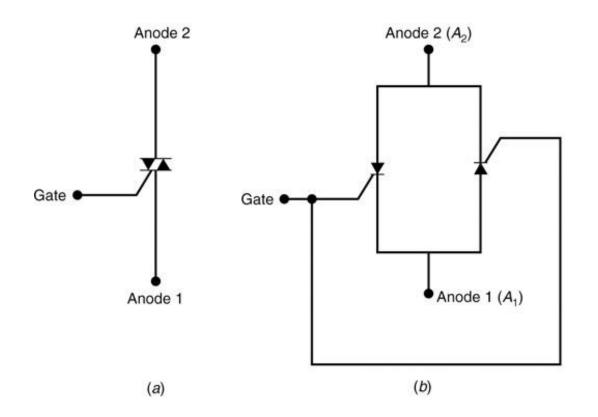
The Diac IF o Ai TH VR VBR(R) VBR(F) IH Civcuit Symbol Characteristic Curve It is a two terminal device It Can Conduct Current in either direction when properly activated Conduction occurs when the breakover Noltage is reached with either polarity

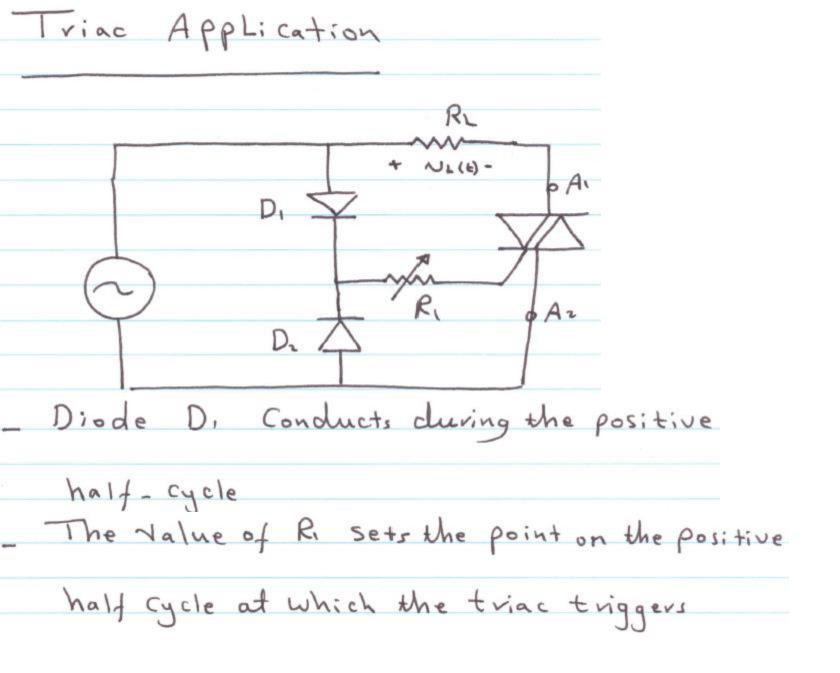
The Diac IF 4 PA. TH VR VBR(R) VBR(F) IH & Az The device turns off when the Current drops below the holding value (IH) The device functions Like two PavalleL Shockley diodes turned in opposite direction

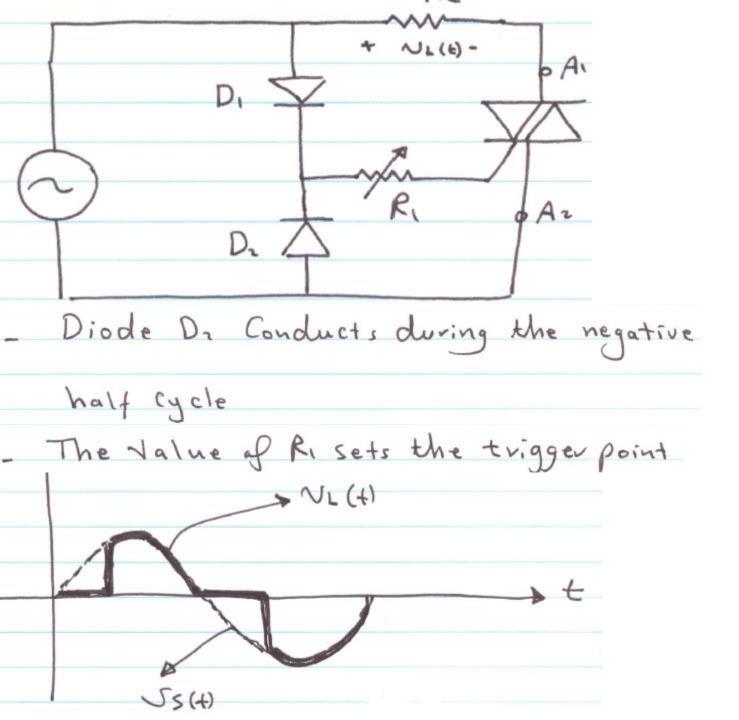




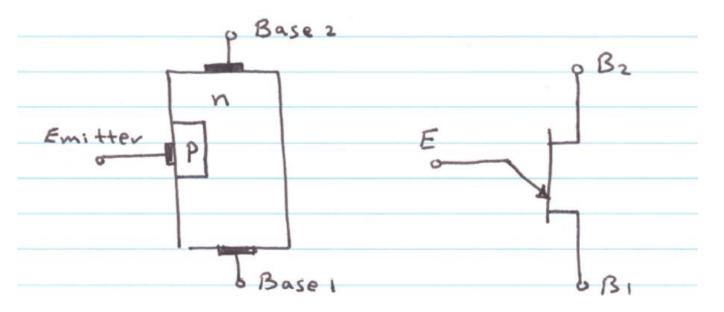


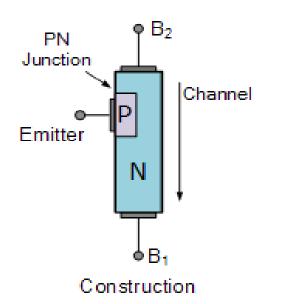


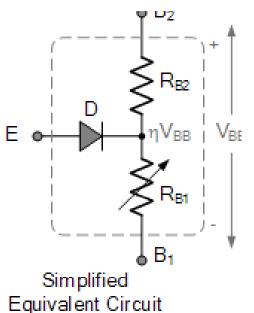




Unijunction Transistor (UJT)

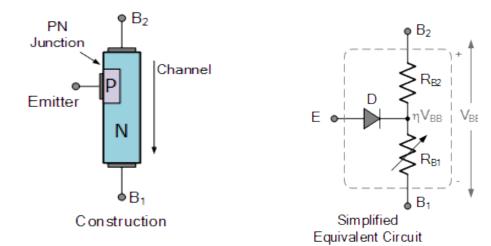






Unijunction Transistors

- The **unijunction transistor** (UJT) is a three-terminal semiconductor device that has only one p-n junction.
- The unijunction transistor (UJT) has two base leads, B₁ and B₂ and an emitter (E) lead.
- The interbase resistance, R_{BB} of a UJT is the resistance of its n-type silicon bar.
- The ratio $R_{B1}/(R_{B1} + R_{B2})$ is called the intrinsic standoff ratio, designated η .

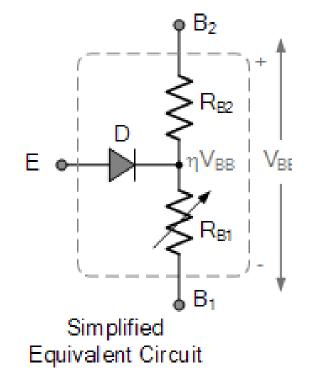


Unijunction Transistor (UJT)

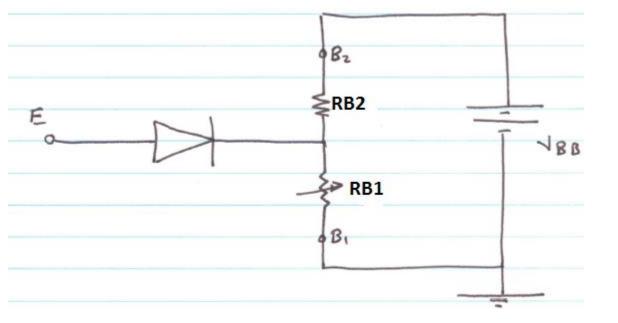
• For a Unijunction transistor, the resistive ratio of R_{B1} to R_{BB} is called the **intrinsic stand-off ratio** (η).

$$\eta = \frac{R_{B1}}{R_{B1} + R_{B2}}$$

 Typical standard values of η range from 0.5 to 0.8 for most common UJT's.



UJTs are used in conjunction with SCRs and Triacs to control their conduction angle



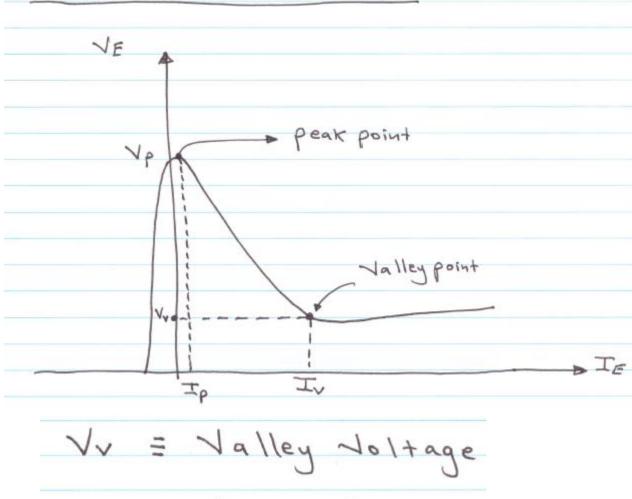
To five the UJT

$$\forall EB_1 > \forall D + \frac{RB1}{RB1 + RB2} \forall BB = \forall \beta$$

 $\forall EB_1 > \forall D + \frac{RB1}{RB1 + RB2} \forall BB = \forall \beta$

$$\int = \frac{RB1}{RBB} = standoff vatio$$

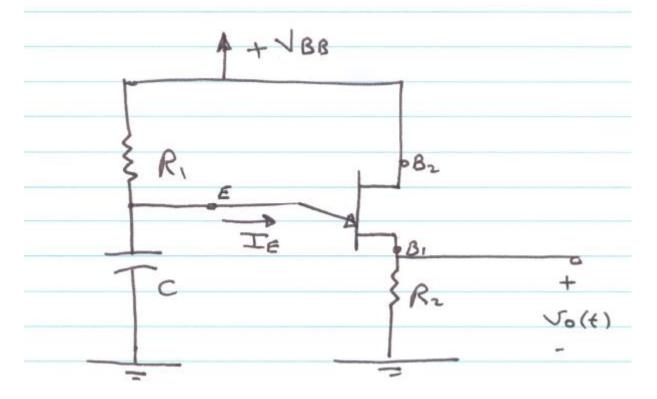
UJT Characteristic Curve

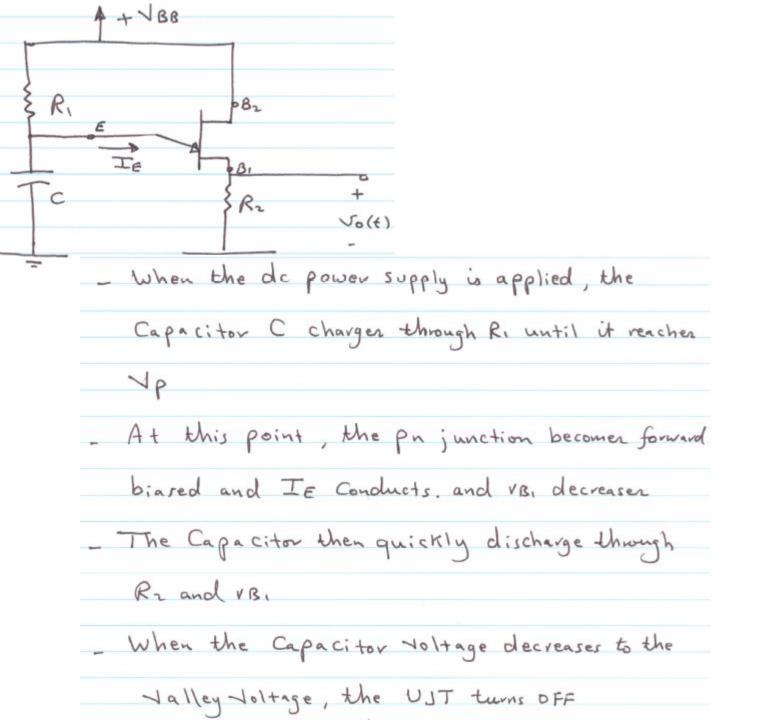


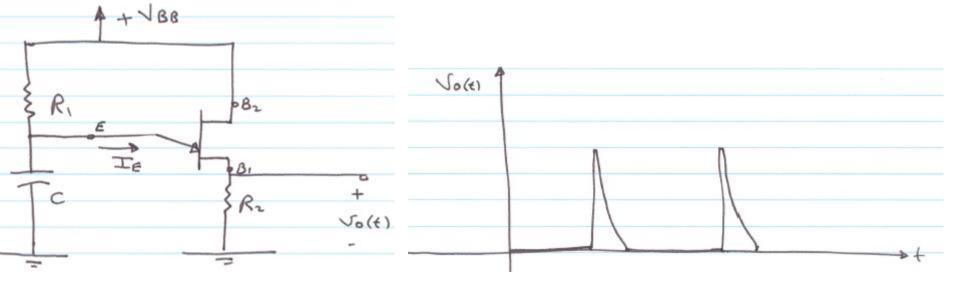
Iv = Valley Current

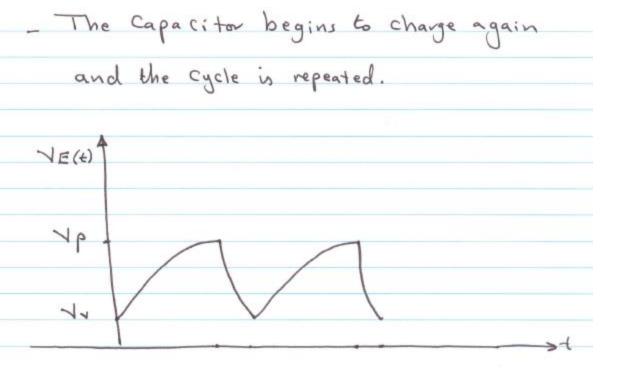
A UJT Application

Relaxation Oscillator









UJT Relaxation Oscillator

